

<b>SPEC SHEET (FOR REFERENCE)</b>	SHEET No.	<b>G05084</b>	Page.
			1 of 1

TYPE : 6PC1802N1T\*\*

CHIP SIZE	0.80 * 0.80 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	23,580 pcs

Maximum Ratings(Ta=25°C)

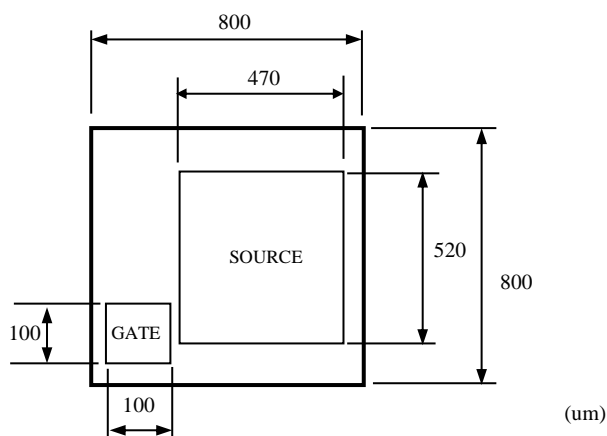
Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	20	V
Gate-source voltage	VGSS	±8	V
Drain Current (DC)	ID	2	A

\* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS			±2	uA	VGS=±8.0V VDS=0V
2	IDSS			500	nA	VDS=20.0V VGS=0V
3	BVDSS	23			V	ID=250uA
4	VTH	0.45		1.0	V	ID=250uA
5	Ron 1		0.045	0.07	Ω	ID=0.95A VGS=4.5V
6	Ron 2		0.06	0.1	Ω	ID=0.67A VGS=2.5V
7	Ron 3		0.11	0.2	Ω	ID=0.67A VGS=1.8V
8	VSD			0.9	V	IS=1A

※ Built-in ZD between Gate and Source.



TENTATIVE

NOTE: